

D-band CMOS 4-way Power Combiner/Divider

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Background

- 1. A power combiner is an important passive device to overcome the limitation of output power in millimeter-wave transmitters.
- 2. A Wilkinson power combiner is widely used to combine output power of each power amplifier (PA) with high isolation between two input ports. However, an

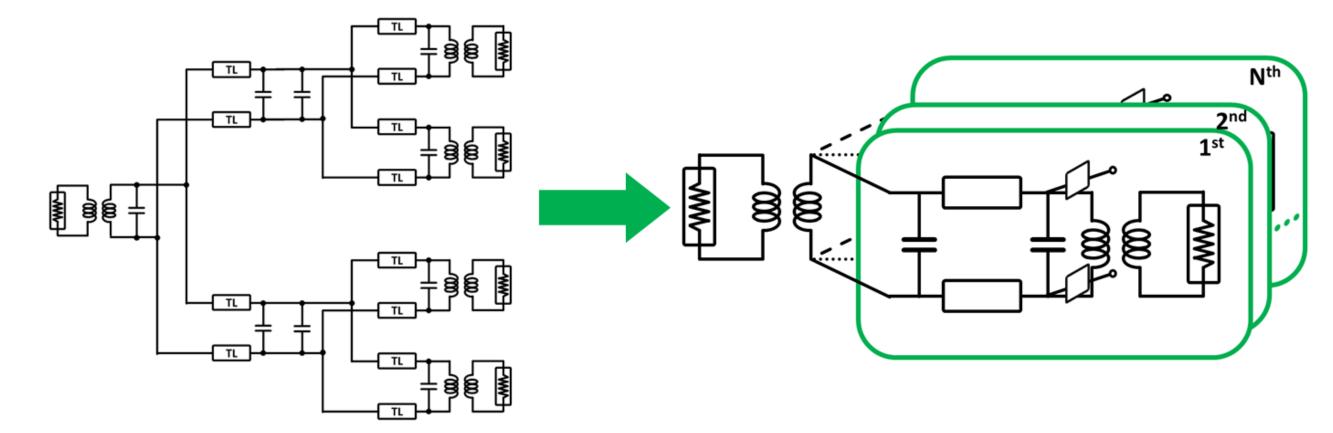
additional matching network is required in the power combining architecture using the conventional WPC because an output impedance of the PA, which is

optimized at a low impedance for increasing output power, should be transformed to the reference impedance.

3. In this project, a compact and low-loss power combiner which have both the output combining and impedance matching of the transmitter in the D-band is proposed.

Methods

A N-way Wilkinson power combiner/divider



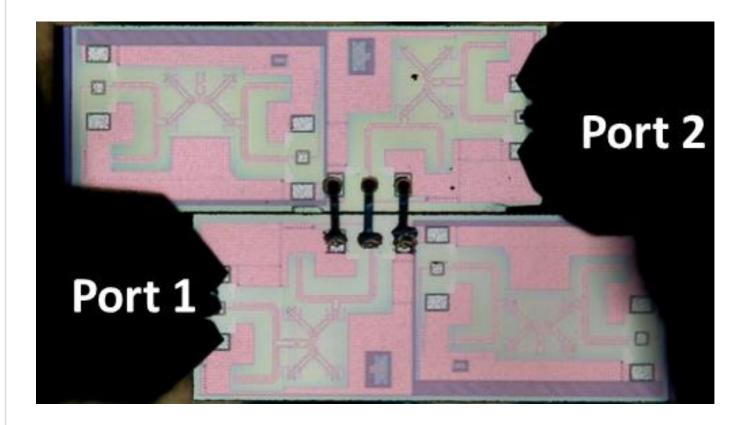
<Parallel type power combiner/divider>

<N-way power combiner/divider>

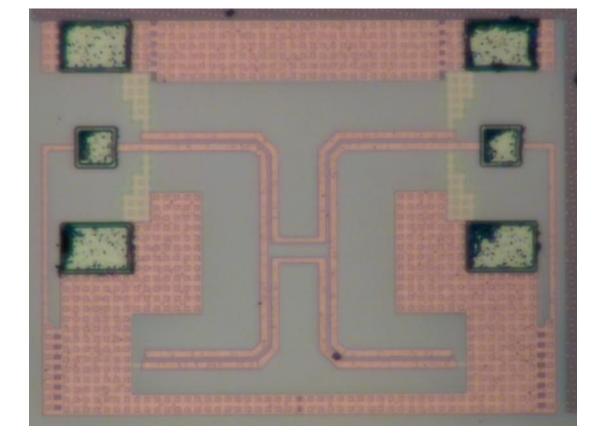
- Design achieves better performance in size and loss characteristic
- Capacitive Loading Technique

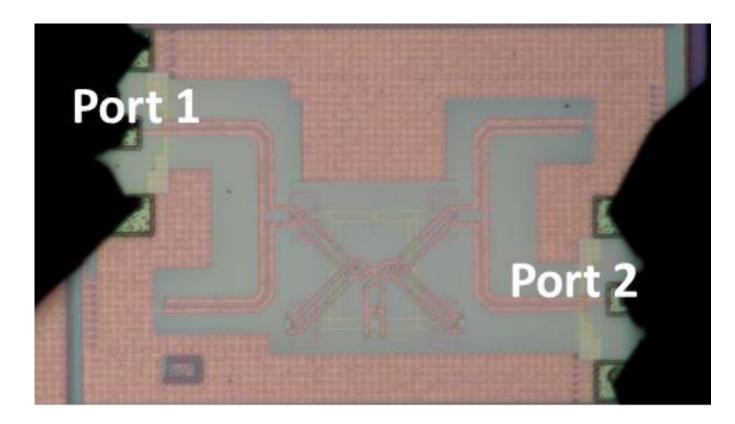
Results

Chip micrograph —

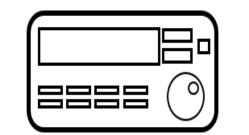


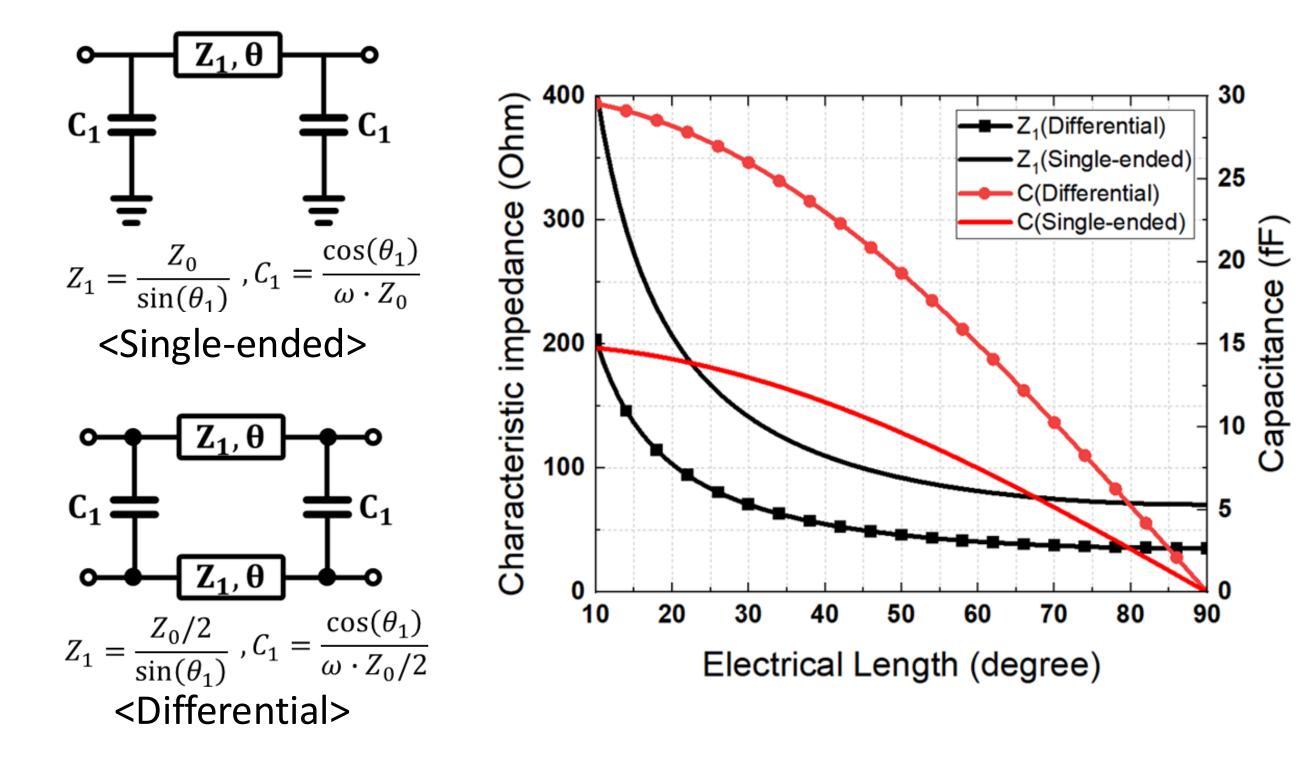
<Insertion loss>



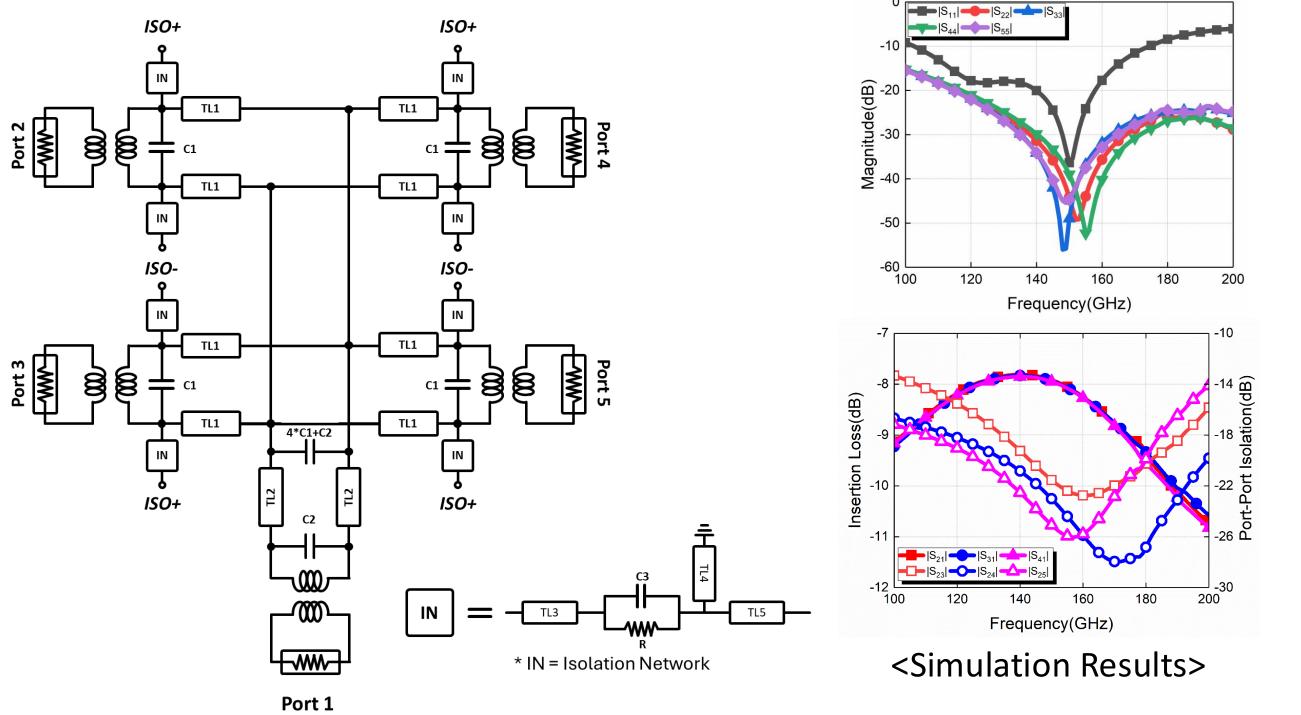


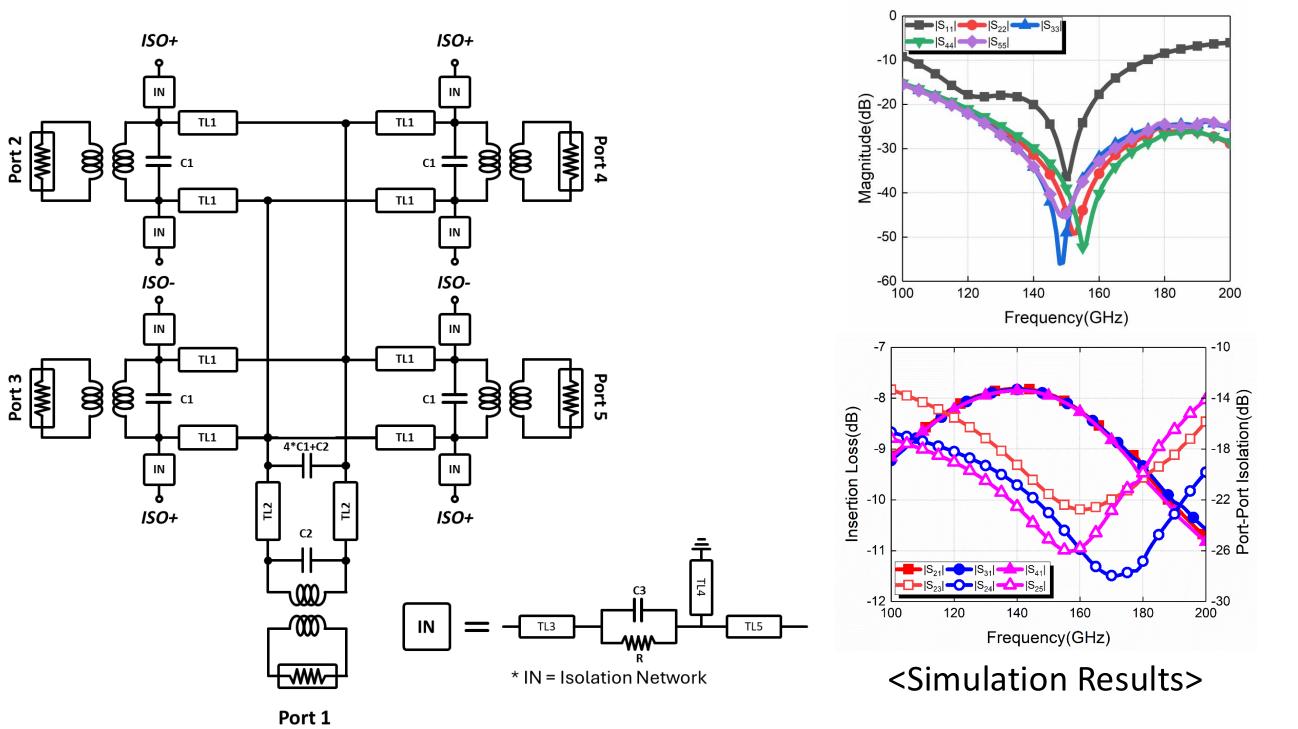
<Port-Port Isolation>





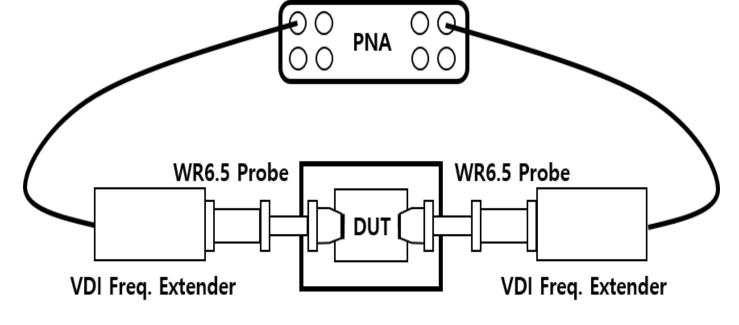
- Smaller design is possible in differential structure
- A proposed power combiner/divider



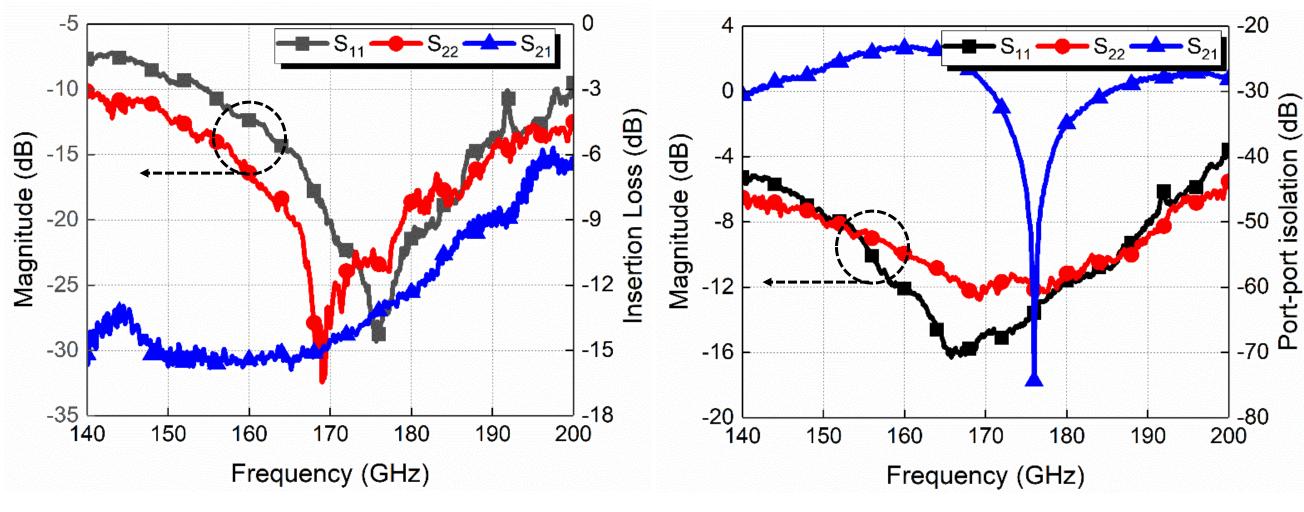


<Balun test pattern>

Measurement Results



<Measurement Setup>



<S-parameter Results>

- Differences between simulated and measured results were induced by the
 - incorrect balun dimensions and the wire bonding added during the

- 4-way Differential Power Combiner/Divider
- 1.79 dB Minimum Loss at 150 GHz

measurement stage

Conclusion

A compact size and low loss 4-way power combiner using capacitive loading

technique is proposed for the D-band high power transmitter

< Acknowledge >

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